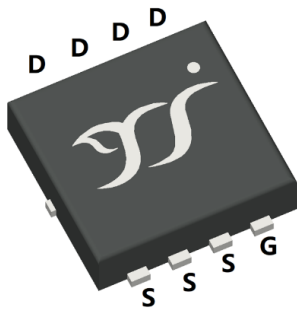
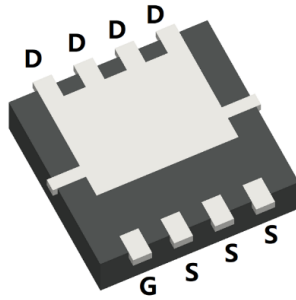


## N-Channel Enhancement Mode Field Effect Transistor

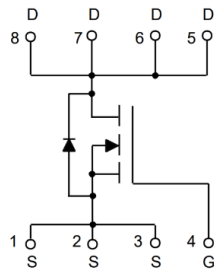


Top View



Bottom View

**PDFN3333-8L**



### Product Summary

- $V_{DS}$  30V
- $I_D$  100A
- $R_{DS(ON)}$  ( at  $V_{GS}=10V$ )  $<2.1m\Omega$
- $R_{DS(ON)}$  ( at  $V_{GS}=4.5V$ )  $<4.5m\Omega$
- 100% EAS Tested
- 100%  $\nabla V_{DS}$  Tested

### General Description

- Split gate trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low  $R_{DS(ON)}$
- Moisture Sensitivity Level 1
- Epoxy Meets UL 94 V-0 Flammability Rating
- Halogen Free

### Applications

- Power switching application
- Uninterruptible power supply
- DC-DC converter

### ■ Absolute Maximum Ratings ( $T_A=25^\circ C$ unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	30	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25^\circ C$	$I_D$	24	A
	$T_A=100^\circ C$		15	
	$T_C=25^\circ C$		100	
	$T_C=100^\circ C$		63	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	400	A
Avalanche energy <sup>B</sup>		EAS	162	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25^\circ C$	$P_D$	2.5	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		50	
	$T_C=100^\circ C$		20	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55~+150	$^\circ C$

### ■ Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	Steady-State	$R_{\theta JA}$	40	50	$^\circ C/W$
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	2	2.5	

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ100G03AJR	F1	100G03A	5000	10000	100000	13" reel



# YJQ100G03AJR

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA
		V <sub>DS</sub> =30V, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C	-	-	100	
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =250μA	1.2	1.7	2.5	V
Static Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =50A	-	1.6	2.1	mΩ
		V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	1.6	2.1	
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	2.5	4.5	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =50A, V <sub>GS</sub> =0V	-	-	1.2	V
Gate resistance	R <sub>G</sub>	f=1MHz	-	3	-	Ω
Maximum Body-Diode Continuous Current	I <sub>S</sub>		-	-	100	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=500KHz	-	2630	-	pF
Output Capacitance	C <sub>oss</sub>		-	1830	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	100	-	
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =15V, I <sub>D</sub> =50A	-	45	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	17	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	8	-	
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> =50A, di/dt=100A/us	-	40	-	nC
Reverse Recovery Time	t <sub>rr</sub>		-	52	-	ns
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =10V, V <sub>DD</sub> =15V, I <sub>D</sub> =50A R <sub>GEN</sub> =2.2Ω	-	14	-	ns
Turn-on Rise Time	t <sub>r</sub>		-	89	-	
Turn-off Delay Time	t <sub>D(off)</sub>		-	27	-	
Turn-off fall Time	t <sub>f</sub>		-	23	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. T<sub>J</sub>=25°C, V<sub>DD</sub>=25V, V<sub>G</sub>=10V, R<sub>G</sub>=25Ω, L=1mH, I<sub>AS</sub>=18A.

C. P<sub>d</sub> is based on max. junction temperature, using junction-case thermal resistance.

D. The value of R<sub>θJA</sub> is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in the still air environment with T<sub>A</sub> =25°C. The maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design.



# YJQ100G03AJR

## Typical Electrical and Thermal Characteristics Diagrams

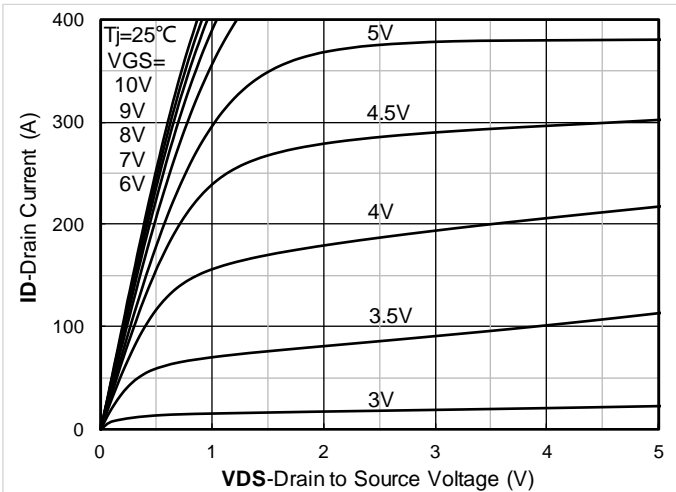


Figure 1. Output Characteristics

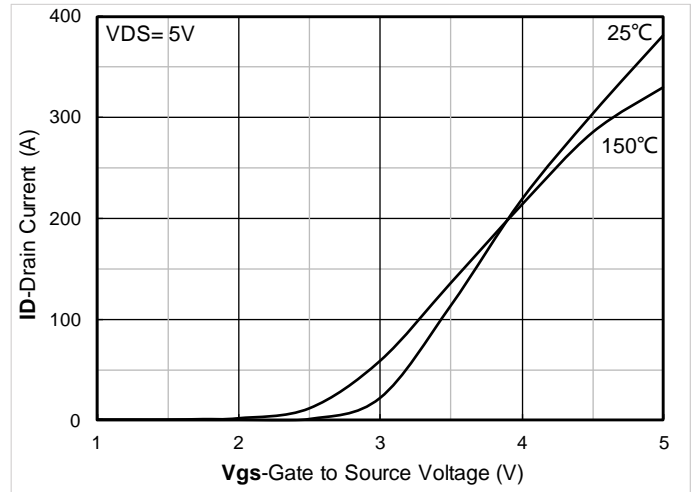


Figure 2. Transfer Characteristics

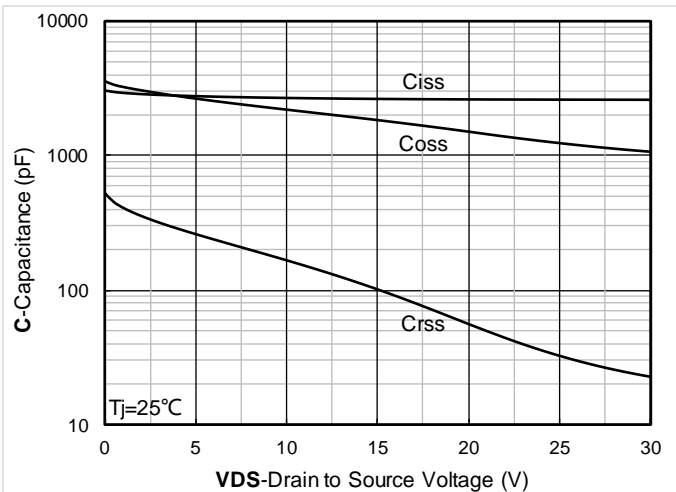


Figure 3. Capacitance Characteristics

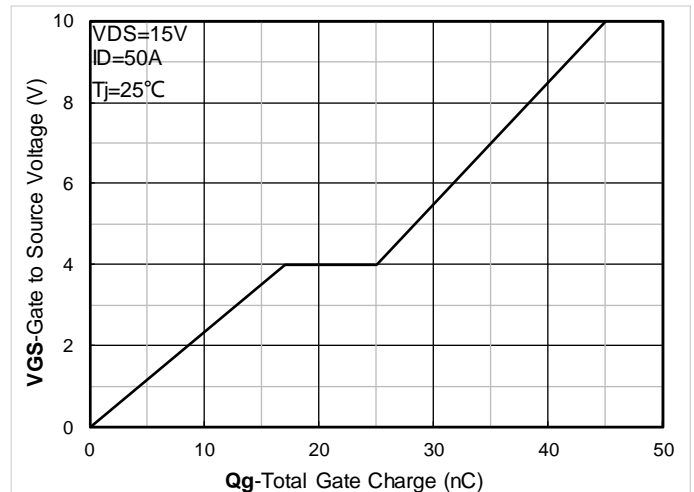


Figure 4. Gate Charge

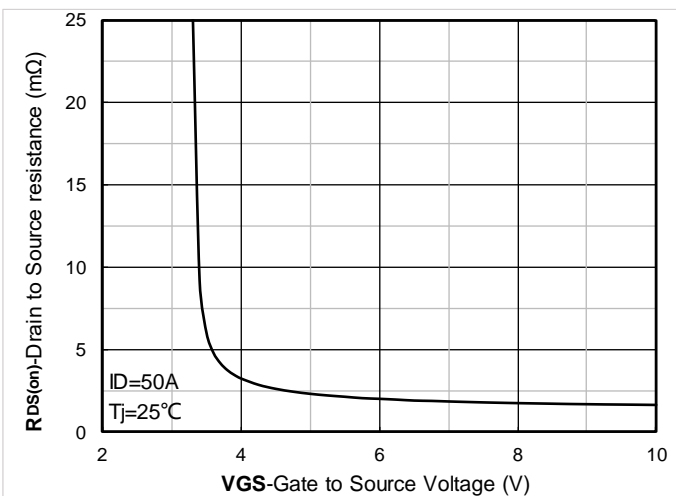


Figure 5. On-Resistance vs Gate to Source Voltage

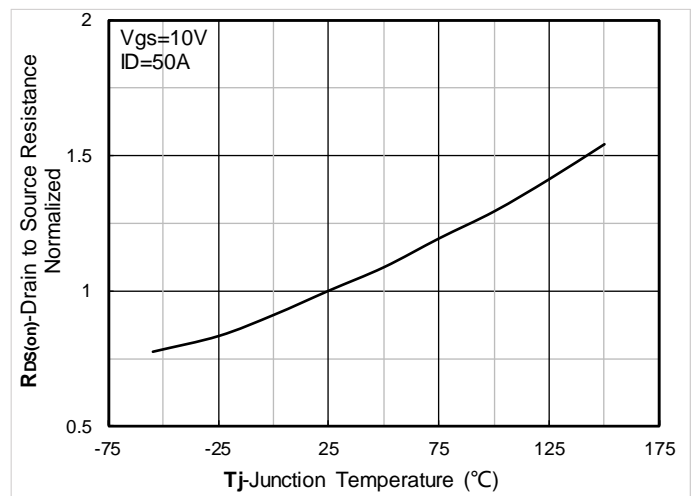


Figure 6. Normalized On-Resistance



# YJQ100G03AJR

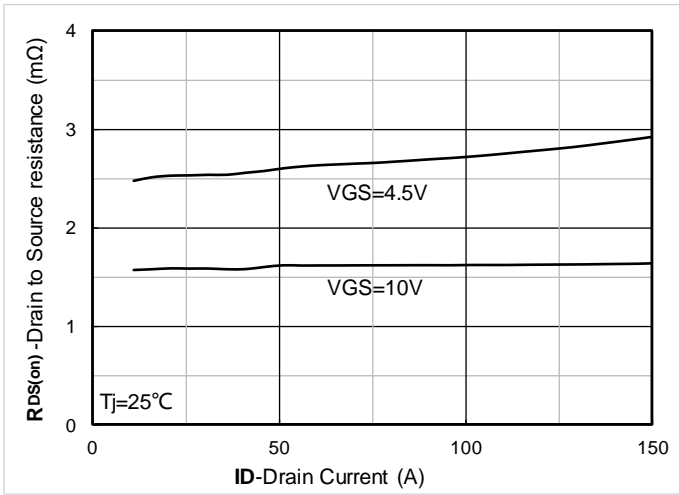


Figure 7. RDS(on) VS Drain Current

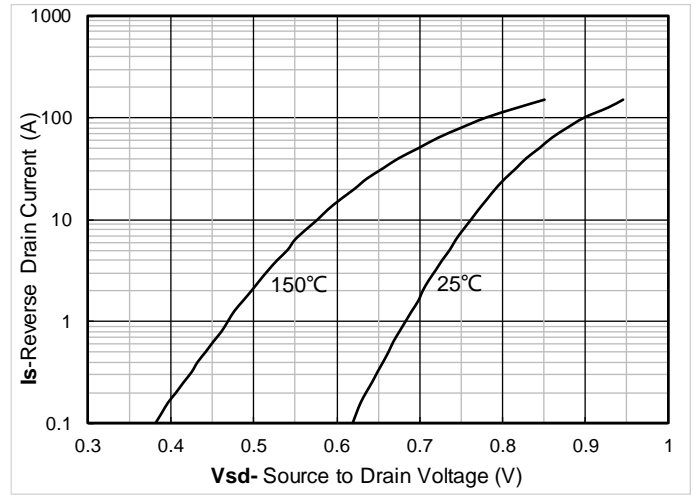


Figure 8. Forward characteristics of reverse diode

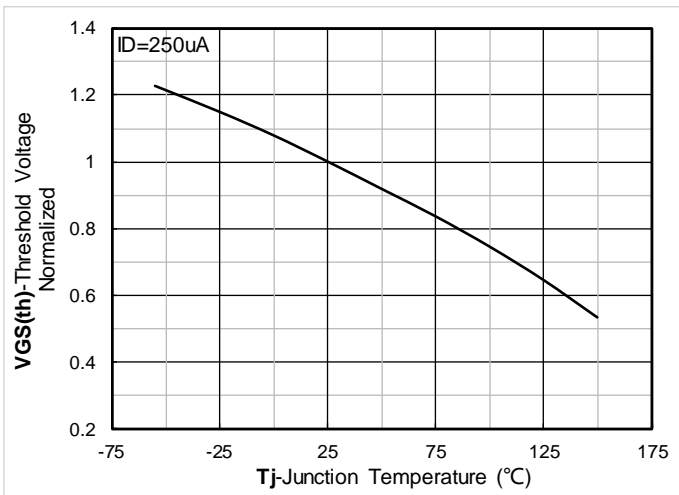


Figure 9. Normalized Threshold voltage

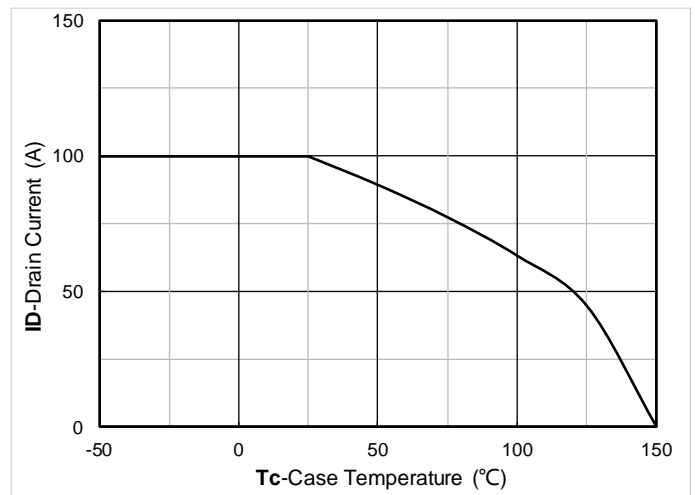


Figure 10. Current dissipation

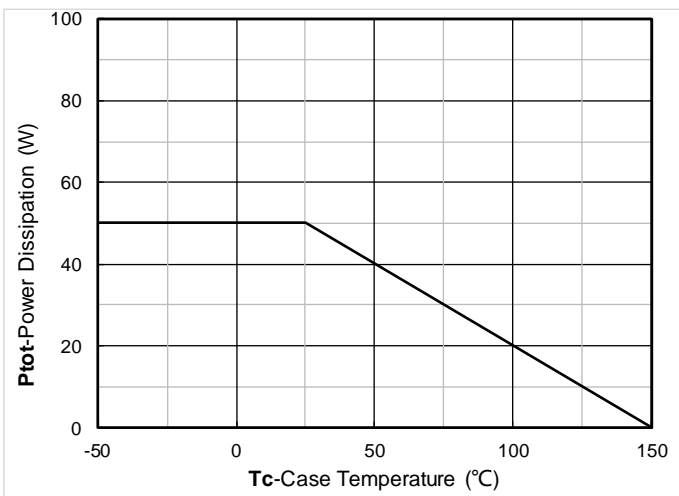


Figure 11. Power dissipation

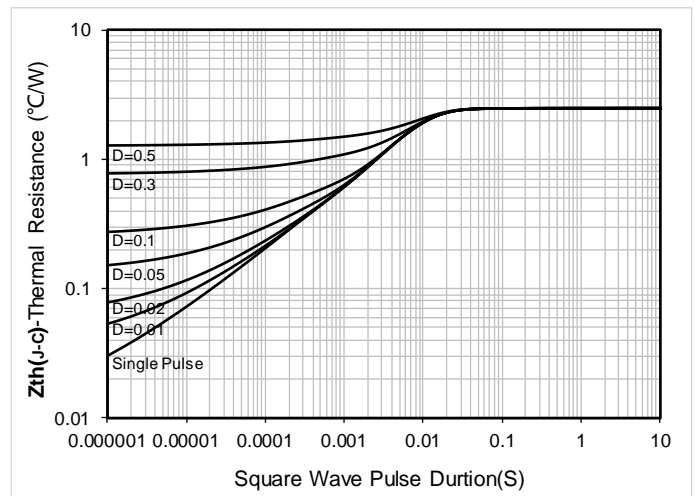


Figure 12. Maximum Transient Thermal Impedance

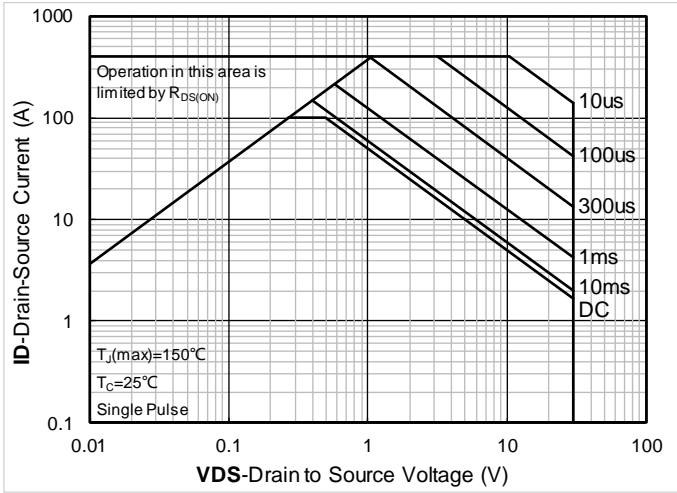


Figure 13. Safe Operation Area

## ■ Test Circuits & Waveforms

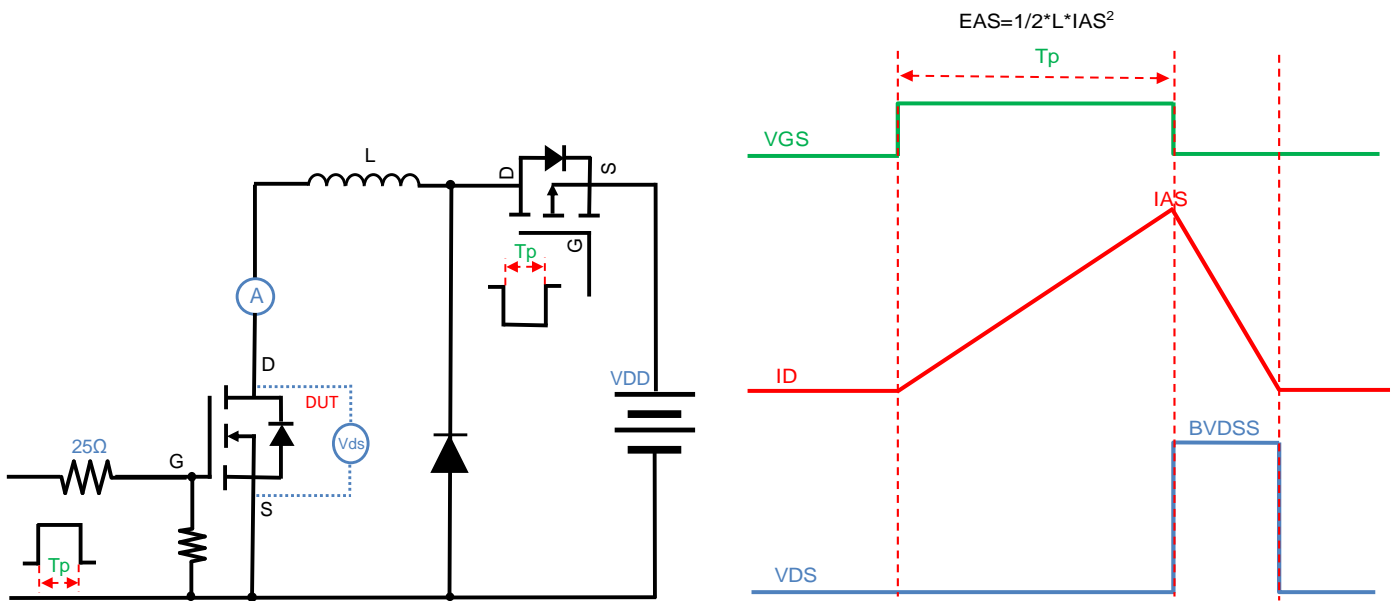


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

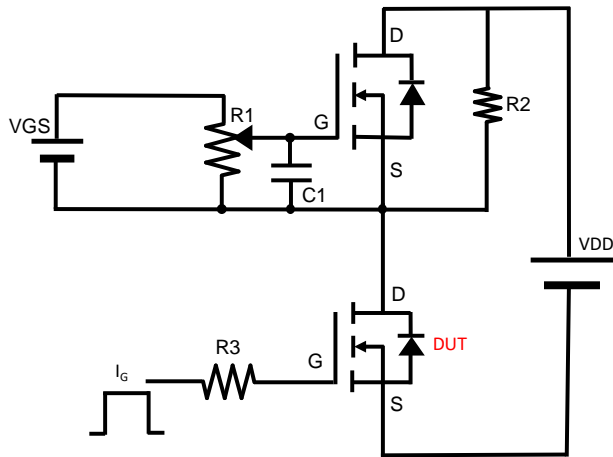


Figure B. Gate Charge Test Circuit & Waveform

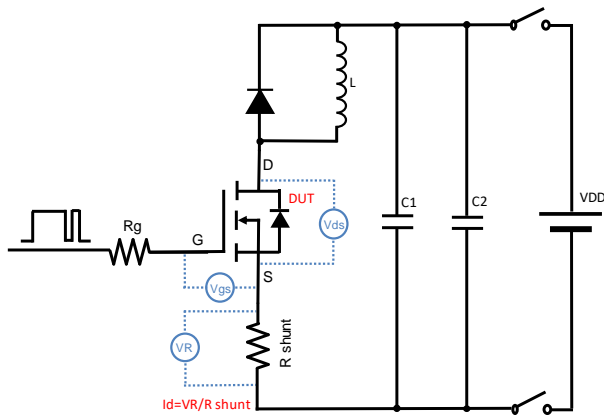


Figure C. Resistive Switching Test Circuit & Waveform

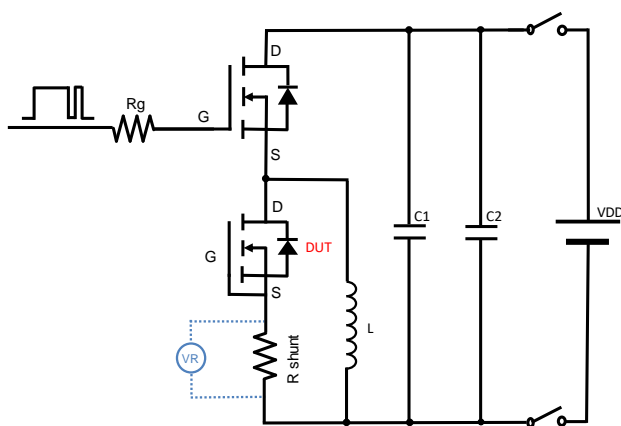
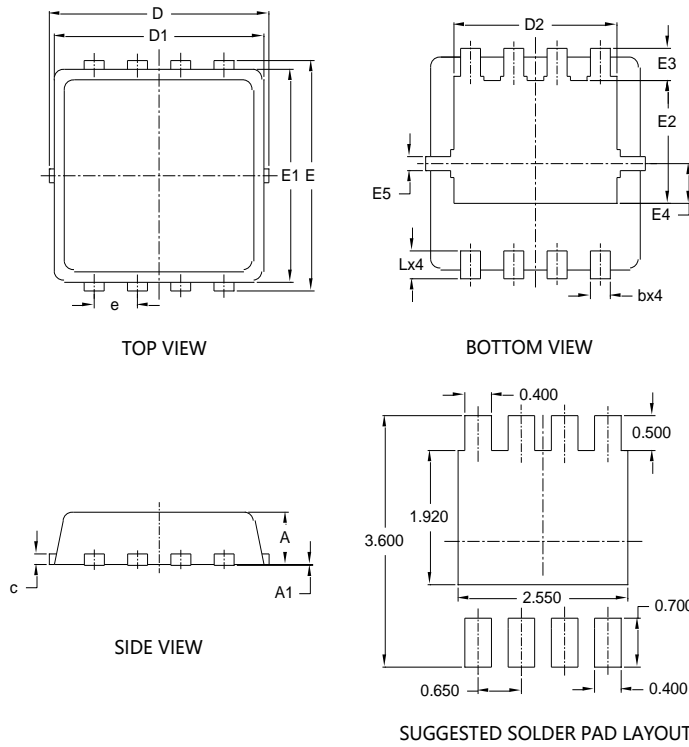


Figure D. Diode Recovery Test Circuit & Waveform



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## ■ PDFN3333-8L Package information



SYMBOL	DIMENSIONS			
	INCHES		Millimeter	
	MIN.	MAX.	MIN.	MAX.
A	0.028	0.033	0.700	0.850
A1	0.000	0.002	0.000	0.050
b	0.008	0.016	0.200	0.400
c	0.004	0.010	0.100	0.250
D	0.124	0.136	3.150	3.450
D1	0.118	0.130	3.000	3.300
D2	0.089	0.104	2.250	2.650
E	0.124	0.136	3.150	3.450
E1	0.114	0.126	2.900	3.200
E2	0.061	0.076	1.540	1.940
E3	0.011	0.026	0.280	0.650
E4	0.022 REF		0.570 REF	
E5	0.008 REF		0.200 REF	
e	0.026 BSC		0.650 BSC	
L	0.012	0.020	0.300	0.500

NOTE:  
 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.  
 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.  
 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

UNIT: mm



## YJQ100G03AJR

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